

ABSTRACT OF THE DISCLOSURE

5 A non-volatile semiconductor memory device has, at a main surface
of a semiconductor substrate, an uneven shape with recesses and
protrusions repeated continuously and alternately and further includes a
source diffusion layer region having a source region formed from an upper
10 surface of each protrusion to the depth direction of the semiconductor
substrate and a source diffusion layer interconnection formed from a bottom
surface of the recess to the depth direction of the semiconductor substrate
when the semiconductor substrate is viewed two-dimensionally. The depth
15 of the bottom surface of the source region from the upper surface of the
protrusion is made equal to or larger than the depth of the bottom surface of
the recess from the upper surface of the protrusion. Thus, a non-volatile
semiconductor memory device is provided which is suitable for
miniaturization and in which resistance of the source diffusion layer region
can easily be lowered.